

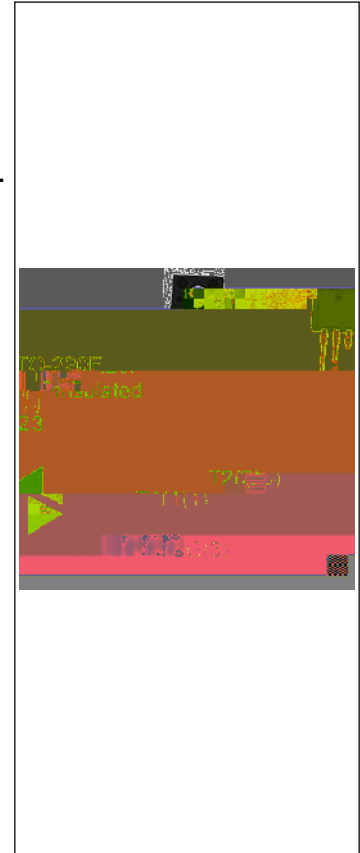


JST12F-800SW 12A TRIAC

Rev.A.1.1

DESCRIPTION:

The JST12F-800SW triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. JST12F-800SW snubberless triac is especially recommended for use on inductive loads. It can be driven directly through the MCU I/O port. By using an external plastic package, JST12F-800SW provides a rated insulation voltage of 2000 VRMS, complying with UL standards (File ref: E252906). Package TO-220F is RoHS compliant.



MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	12	A
V_{DRM}/V_{RRM}	800	V
$I_{GT} / /$	10/10/10	mA

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	
Operating junction temperature range	T_j	-40-125	
Repetitive peak off-state voltage ($T_j=25^\circ C$)	V_{DRM}	800	V
Repetitive peak reverse voltage ($T_j=25^\circ C$)	V_{RRM}	800	V
RMS on-state current ($T_c=85^\circ C$)	$I_{T(RMS)}$	12	A
Non repetitive surge peak on-state current (full cycle, $t_p=20ms$, $T_j=25^\circ C$)	I_{TSM}	120	A
Non repetitive surge peak on-state current (full cycle, $t_p=16.6ms$, $T_j=25^\circ C$)		132	
I^2t value for fusing ($t_p=10ms$, $T_j=25^\circ C$)	I^2t	72	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$, $f=100Hz$, $T_j=125^\circ C$)	di/dt	50	$A/\mu s$
Peak gate current ($t_p=20\mu s$, $T_j=125^\circ C$)	I_{GM}	4	A



Average gate power dissipation ($T_j=125$)	$P_{G(AV)}$	0.5	W
Peak gate power	P_{GM}	10	W
Peak pulse voltage ($T_j=25$; non-repetitive, off-state; FIG.7)	V_{pp}	4	kV

ELECTRICAL CHARACTERISTICS ($T_j=25$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12V$ $R_L=33$	- -	MAX.	10	mA
V_{GT}		- -	MAX.	1	V
V_{GD}	$V_D=V_{DRM}$ $T_j=125$ $R_L=3.3k$	- -	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	-	MAX.	25	mA
				30	
I_H	$I_T=500mA$		MAX.	15	mA
dV/dt	$V_D=540V$ Gate Open $T_j=125$		MIN.	400	V/ μs
(dI/dt)c	(dV/dt)c=10V/ μs $T_j=125$		MIN.	3	A/ms

t_{on} $I_G=20mA$ $I_A=200mA$ $I_R=20mA$
T

FIG.1: Maximum power dissipation versus RMS on-state current

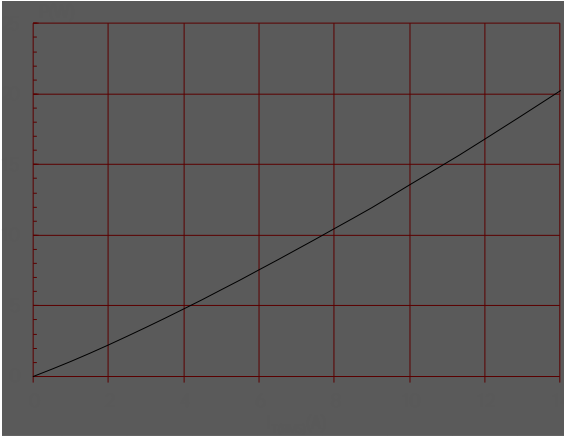


FIG.2: RMS on-state current versus case temperature

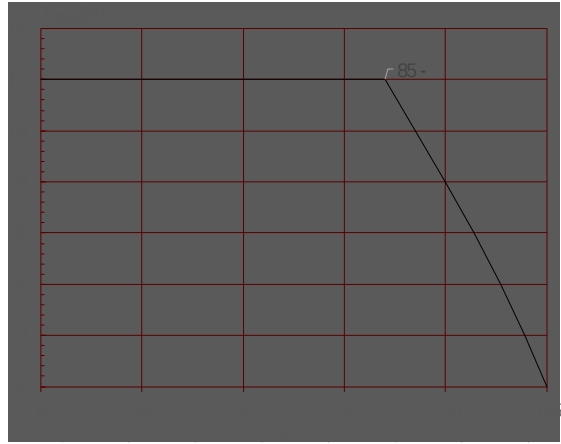


FIG.3: Surge peak on-state current versus number of cycles

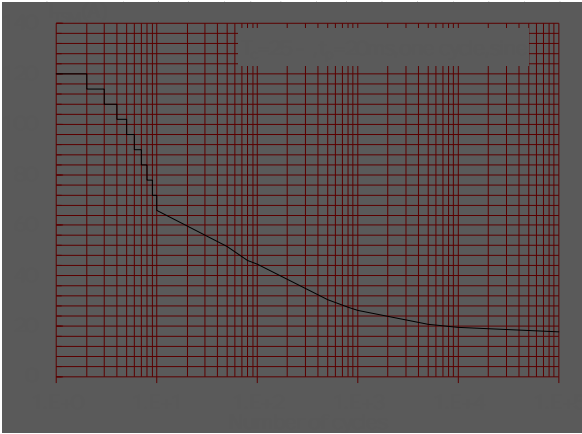
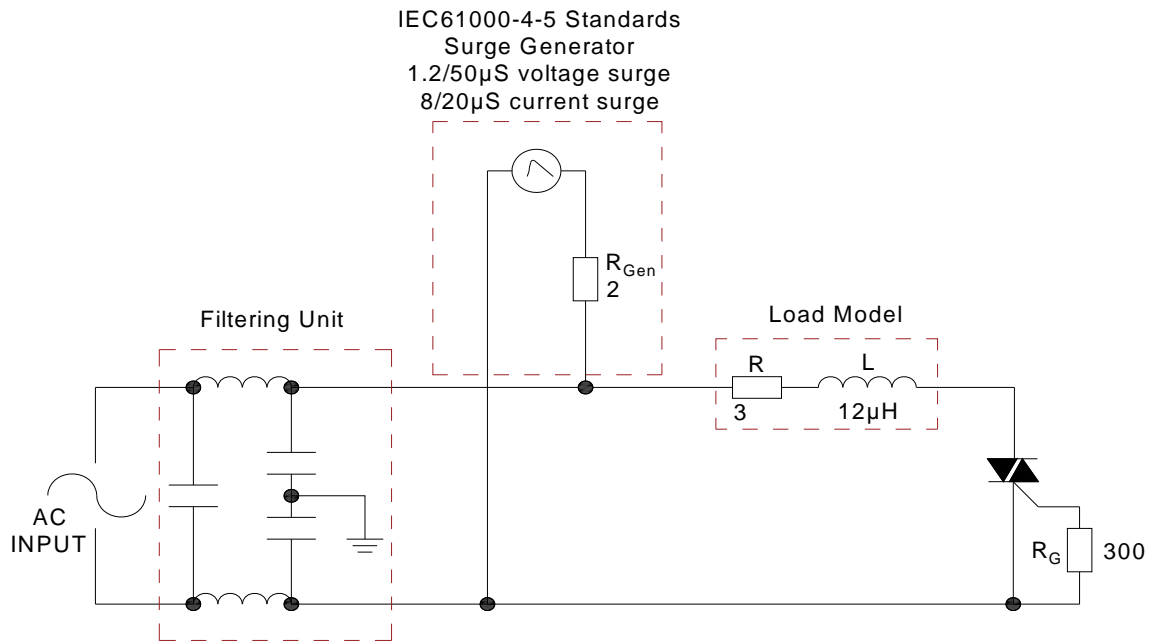


FIG.4: On-state characteristics

FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



LEAD FORMING AND SOLDERING

Refer to the application note “Assembly Instructions for Thyristors in Through-hole Package” released by JieJie Microelectronics.



ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
		H- I- J			
JST12F-800SW	800				

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